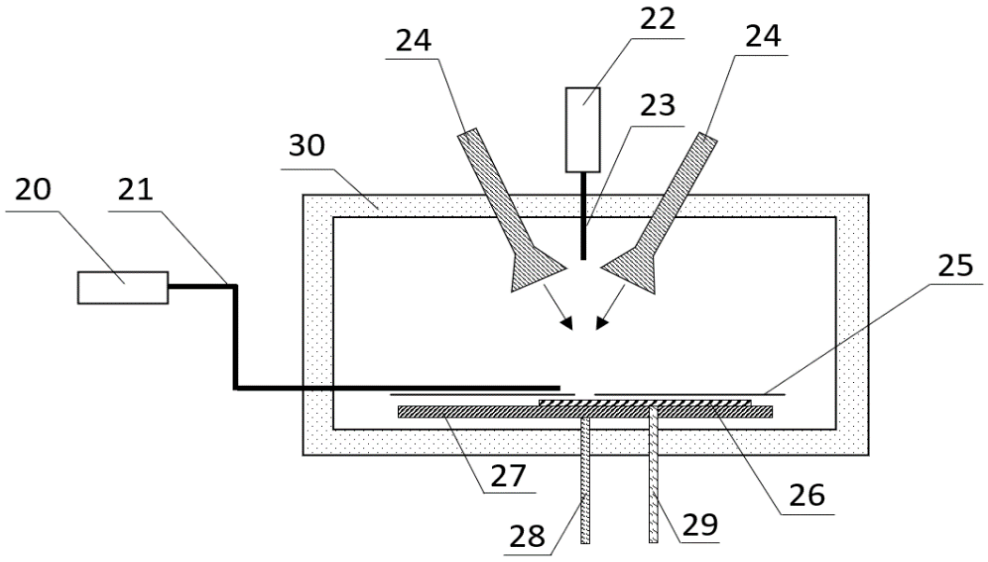

22
24
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29

FIG. 1

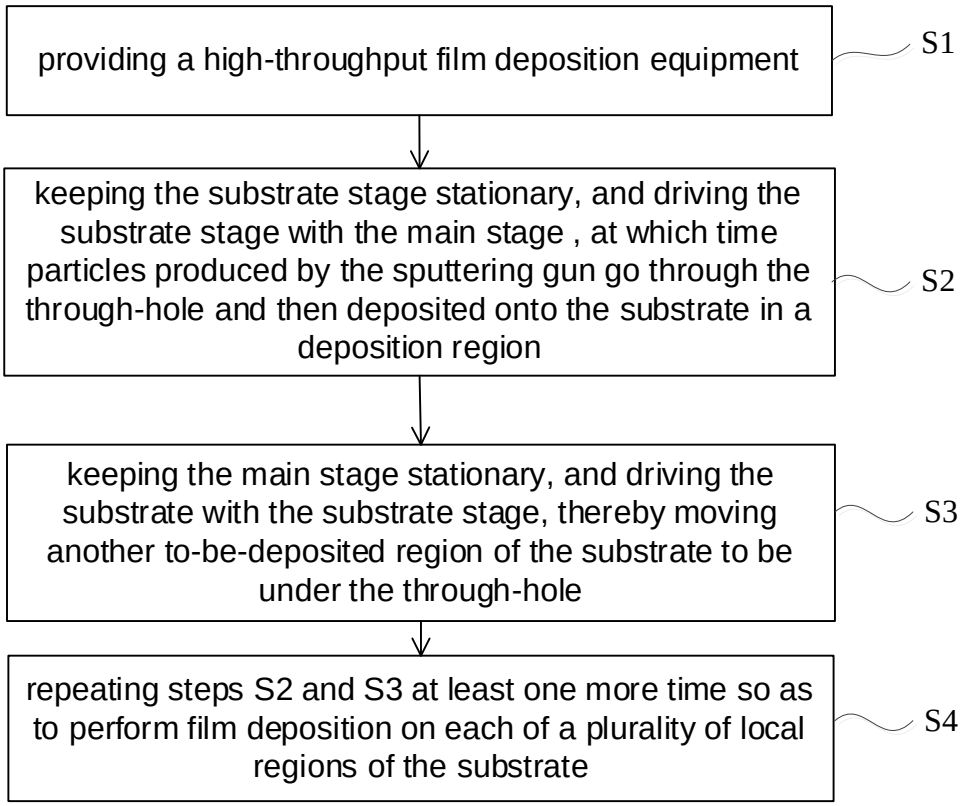

providing a high-throughput film deposition equipment
S1
keeping the substrate stage stationary, and driving the substrate stage with the main stage , at which time particles produced by the sputtering gun go through the through-hole and then deposited onto the substrate in a deposition region
S2
keeping the main stage stationary, and driving the substrate with the substrate stage, thereby moving another to-be-deposited region of the substrate to be under the through-hole
S3
repeating steps S2 and S3 at least one more time so as to perform film deposition on each of a plurality of local regions of the substrate
S4

FIG. 2

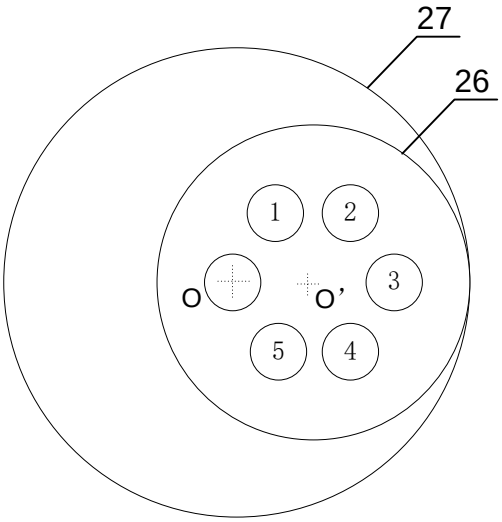

27
26
1
2
O
O'
3
5
4

FIG. 3

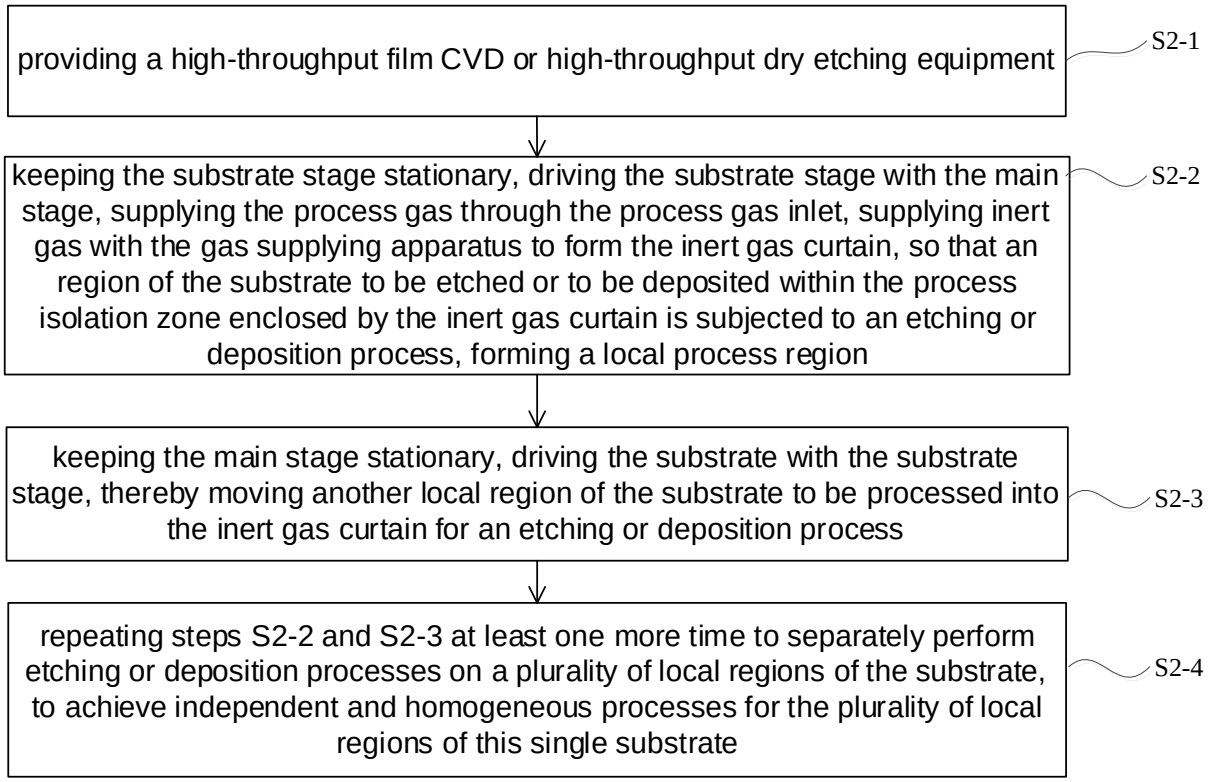

providing a high-throughput film CVD or high-throughput dry etching equipment
S2-1
keeping the substrate stage stationary, driving the substrate stage with the main stage, supplying the process gas through the process gas inlet, supplying inert gas with the gas supplying apparatus to form the inert gas curtain, so that an region of the substrate to be etched or to be deposited within the process isolation zone enclosed by the inert gas curtain is subjected to an etching or deposition process, forming a local process region
S2-2
keeping the main stage stationary, driving the substrate with the substrate stage, thereby moving another local region of the substrate to be processed into the inert gas curtain for an etching or deposition process
S2-3
repeating steps S2-2 and S2-3 at least one more time to separately perform etching or deposition processes on a plurality of local regions of the substrate, to achieve independent and homogeneous processes for the plurality of local regions of this single substrate
S2-4

FIG. 4

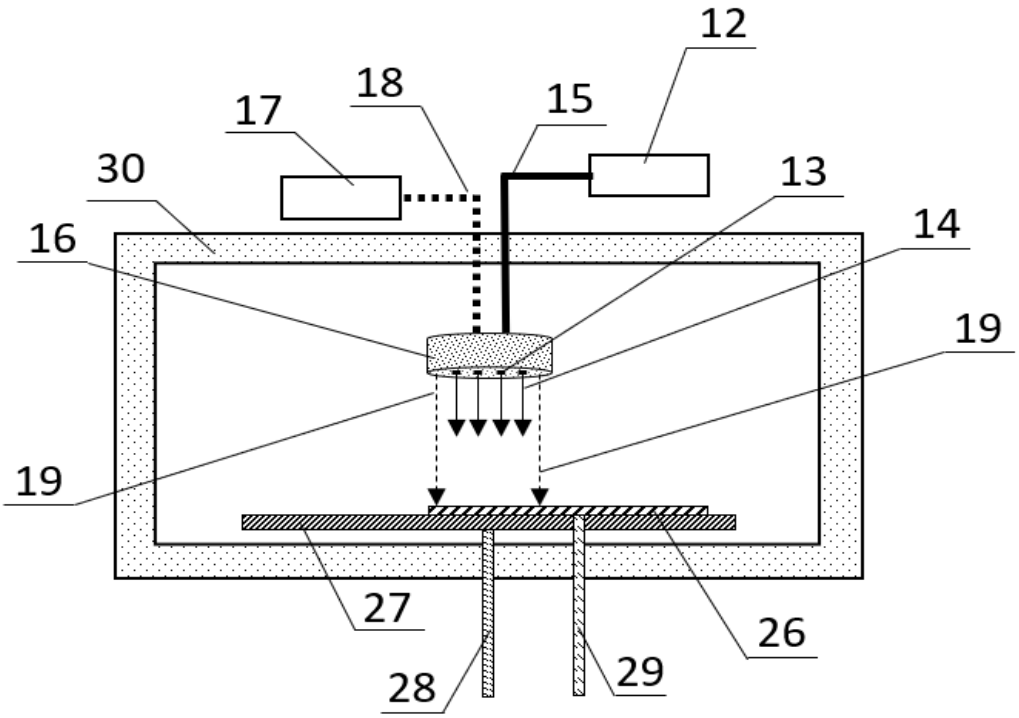


FIG. 5